

# HT27LC512 CMOS 64K×8-Bit OTP EPROM

#### **Features**

- 64K×8-bit organization
- Single +3.3V power supply
- · Programming voltage
  - V<sub>PP</sub>=12.2V±0.2V
  - V<sub>CC</sub>=5.8V±0.2V
- · Low power consumption
  - Active: 15mA max.Standby: 1µA typ.
- Fast read access time: 120ns
  CMOS and TTL compatible I/O
- · Commercial and industrial temperature range

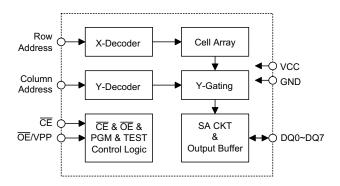
- · Fast programming algorithm
- Read access time: 90ns
- Programming time 75µs typ.
- · High-reliability CMOS technology
- Latch-up immunity to 100mA from -1.0V to V<sub>CC</sub>+1.0V
- Two line control (OE & CE)
- · Standard product identification code
- Commercial temperature ranges (0°C to +70°C)
- 28-pin DIP/SOP/TSOP, 32-pin PLCC package

### **General Description**

The HT27LC512 chip family is a low-power, 512K bit, +3.3V electrically one-time programmable (OTP) read-only memories (EPROM). Organized into 64K words with 8 bits per word, it features a fast single address location programming, typically at 75µs per byte. Any byte can be accessed in less than 90ns with respect

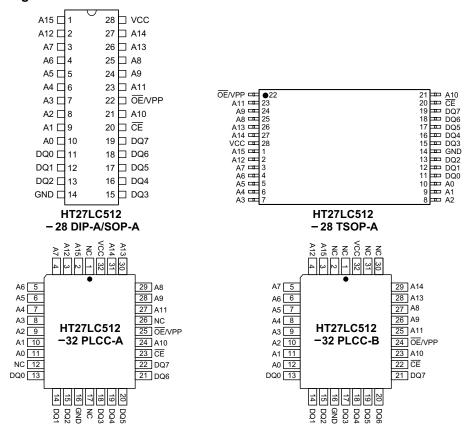
to Spec. This eliminates the need for WAIT states in high-performance microprocessor systems. The HT27LC512 has separate Output Enable  $(\overline{OE})$  and Chip Enable  $(\overline{CE})$  controls which eliminate bus contention issues.

#### **Block Diagram**





### **Pin Assignment**



#### **Pin Description**

Pin Name	I/O/C/P	Description			
A0~A15	ı	Address inputs			
DQ0~DQ7	I/O	Data inputs/outputs			
CE	С	Chip enable			
OE/VPP	C/P	Output enable/program voltage supply			
NC	_	No connection			

### **Absolute Maximum Ratings**

Operation Temperature Commercial	0°C to +70°C
Storage Temperature	65℃ to 125°C
Applied VCC Voltage with Respect to GND	0.6V to 7.0V
Applied Voltage on Input Pin with Respect to GND	0.6V to 7.0V
Applied Voltage on Output Pin with Respect to GND	0.6V to V <sub>CC</sub> +0.5V
Applied Voltage on A9 Pin with Respect to GND	0.6V to 13.5V
Applied VPP Voltage with Respect to GND	0.6V to 13.5V
Applied READ Voltage (Functionality is guaranteed between these limits)	+3V to +3.6V

Note: These are stress ratings only. Stresses exceeding the range specified under. "Absolute Maximum Ratings" may cause substantial damage to the device. Functional operation of this device at other conditions beyond those listed in the specification is not implied and prolonged exposure to extreme conditions may affect device reliability.



### **D.C. Characteristics**

Cumbal	Doromatar		Test Conditions	N#:	Ti	Max.	Unit
Symbol	Parameter	Vcc	Conditions	Min.	Тур.	wax.	
Read op	eration	•					
V <sub>OH</sub>	Output High Level	3.3V	I <sub>OH</sub> =-0.4mA	2.4	_	_	V
V <sub>OL</sub>	Output Low Level	3.3V	I <sub>OL</sub> =2.0mA	_	_	0.45	V
$V_{IH}$	Input High Level	3.3V	_	2.0	_	V <sub>CC</sub> +0.5	V
V <sub>IL</sub>	Input Low Level	3.3V	_	0.3	_	0.8	V
ILI	Input Leakage Current	3.3V	V <sub>IN</sub> =0 to 3.6V	5	_	5	μΑ
I <sub>LO</sub>	Output Leakage Current	3.3V	V <sub>OUT</sub> =0 to 3.6V	10	_	10	μΑ
Icc	VCC Active Current	3.3V	CE=V <sub>IL</sub> , f=5MHz, I <sub>OUT</sub> =0mA	_	_	15	mA
I <sub>SB1</sub>	Standby Current (CMOS)	3.3V	CE=V <sub>CC</sub> ±0.3V	_	1.0	10	μΑ
I <sub>SB2</sub>	Standby Current (TTL)	3.3V	CE=V <sub>IH</sub>	_	_	0.6	mA
I <sub>PP</sub>	VPP Read/Standby Current	3.3V	CE=OE=V <sub>IL</sub> , V <sub>PP</sub> =V <sub>CC</sub>	_	_	100	μΑ
Program	ming operation	'					
V <sub>OH</sub>	Output High Level	5.8V	I <sub>OH</sub> =0.4mA	2.4	_	_	V
V <sub>OL</sub>	Output Low Level	5.8V	I <sub>OL</sub> =2.1mA	_	_	0.45	V
V <sub>IH</sub>	Input High Level	5.8V	_	0.7V <sub>CC</sub>	_	V <sub>CC</sub> +0.5	V
V <sub>IL</sub>	Input Low Level	5.8V	_	-0.5	_	0.8	V
I <sub>LI</sub>	Input Load Current	5.8V	V <sub>IN</sub> =V <sub>IL</sub> , V <sub>IH</sub>	_	_	5.0	μΑ
$V_{H}$	A9 Product ID Voltage	5.8V	_	11.5	_	12.5	V
Icc	VCC Supply Current	5.8V	_	_	_	40	mA
I <sub>PP</sub>	VPP Supply Current	5.8V	CE=V <sub>IL</sub>	_	_	10	mA
Capacita	ince					· '	
C <sub>IN</sub>	Input Capacitance	3.3V	V <sub>IN</sub> =0V	_	8	12	pF
C <sub>OUT</sub>	Output Capacitance	3.3V	V <sub>OUT</sub> =0V		8	12	pF
C <sub>VPP</sub>	VPP Capacitance	3.3V	V <sub>PP</sub> =0V	_	18	25	pF

### A.C. Characteristics

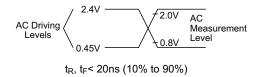
Ta=+25°C±5°C

Cumbal	Parameter		Test Conditions	N4:	T		Unit
Symbol	Parameter	Vcc	Conditions	Min.	Тур.	Max.	
Read operation							
t <sub>ACC</sub>	Address to Output Delay	3.3V	CE=OE=V <sub>IL</sub>	_	_	90	ns
t <sub>CE</sub>	Chip Enable to Output Delay	3.3V	OE=V <sub>IL</sub>	_	_	90	ns
t <sub>OE</sub>	Output Enable to Output Delay	3.3V	CE=V <sub>IL</sub>	_	_	45	ns
t <sub>DF</sub>	CE or OE High to Output Float, Whichever Occurred First	3.3V	_	_	_	40	ns
t <sub>OH</sub>	Output Hold from Address, CE or OE, Whichever Occurred First	3.3V	_	0	_	_	ns

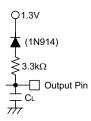


Cumala a l	Damanastan		Test Conditions	M:	Тур.	Max.	Unit		
Symbol	Parameter	Vcc	Conditions	Min.					
Program	Programming operation								
t <sub>AS</sub>	Address Setup Time	5.8V	_	2	_	_	μS		
toes	CE/VPP Setup Time	5.8V	_	2	_	_	μS		
toeh	OE/VPP Hold Time	5.8V	_	2	_	_	μS		
t <sub>DS</sub>	Data Setup Time	5.8V	_	2	_	_	μS		
t <sub>AH</sub>	Address Hold Time	5.8V	_	0	_	_	μS		
t <sub>DH</sub>	Data Hold Time	5.8V	_	2	_	_	μS		
t <sub>DFP</sub>	Output Enable to Output Float Delay		_	0	_	130	ns		
t <sub>PW</sub>	PGM Program Pulse Width	5.8V	_	30	75	105	μS		
t <sub>VCS</sub>	VCC Setup Time		_	2	_	_	μS		
t <sub>DV</sub>	Data Valid From CE	5.8V	_	_	_	150	ns		
t <sub>VR</sub>	OE/VPP Recovery Time	5.8V	_	2	_	_	μS		

#### Test waveforms and measurements



### Output test load



Note:  $C_L$ =100pF including jig capacitance

### **Product Identification Code**

Code	Pins									Hex	
Code	A0	<b>A</b> 1	DQ7	DQ6	DQ5	DQ4	DQ3	DQ2	DQ1	DQ0	Data
Manufacturer	0	1	0	0	0	1	1	1	0	0	1C
Device Type	1	1	1	0	0	0	0	0	1	1	83
O and the same than a	0	0	0	1	1	1	1	1	1	1	7F
Continuation	1	0	0	1	1	1	1	1	1	1	7F



#### **Functional Description**

#### Operation mode

All the operation modes are shown in the table following.

Mode	CE	OE/VPP	A0	A9	Output
Read	V <sub>IL</sub>	V <sub>IL</sub>	X (2)	X	Dout
Output Disable	V <sub>IL</sub>	V <sub>IH</sub>	X	X	High Z
Standby (TTL)	V <sub>IH</sub>	X	X	X	High Z
Standby (CMOS)	V <sub>CC</sub> ± 0.3V	X	X	X	High Z
Program	V <sub>IL</sub>	V <sub>PP</sub>	X	X	D <sub>IN</sub>
Program Verify	V <sub>IL</sub>	V <sub>IL</sub>	X	X	D <sub>OUT</sub>
Product Inhibit	V <sub>IH</sub>	$V_{PP}$	X	X	High Z
Manufacturer Code (3)	V <sub>IL</sub>	V <sub>IL</sub>	V <sub>IL</sub>	V <sub>H</sub> (1)	1C
Device Code (3)	V <sub>IL</sub>	V <sub>IL</sub>	V <sub>IH</sub>	V <sub>H</sub> (1)	83

Note: (1)  $V_H = 12.0V \pm 0.5V$ 

(3) For Manufacturer Code and Device Code, A1=V<sub>IH</sub>, When A1=V<sub>IL</sub>, both codes will read 7F

#### Programming of the HT27LC512

(2) X=Either V<sub>IH</sub> or V<sub>IL</sub>

When the HT27LC512 is delivered, the chip has all 512K bits in the "ONE" or HIGH state. "ZEROs" are loaded into the HT27LC512 through the procedure of programming.

The programming mode is entered when 12.2 $\pm$ 0.2V is applied to the  $\overline{\text{OE}}/\text{VPP}$  pin and  $\overline{\text{CE}}$  is at V<sub>IL</sub>. For programming, the data to be programmed is applied with 8 bits in parallel to the data pins.

The programming flowchart in Figure 3. shows the fast interactive programming algorithm. The interactive algorithm reduces programming time by using 30 µs to 105µs programming pulses and giving each address only as many pulses as is necessary in order to reliably program the data. After each pulse is applied to a given address, the data in that address is verified. If the data is not verified, additional pulses are given until it is verified or until the maximum number of pulses is reached. This process is repeated while sequencing through each address of the HT27LC512. This part of the programming algorithm is carried at  $V_{\text{CC}}$ =5.8V to assure that each EPROM bit is programmed to a sufficiently high threshold voltage. This ensures that all bits have sufficient margin. After the final address is completed, the entire EPROM memory is read at V<sub>CC</sub>=V<sub>PP</sub>=3.3±0.3V to verify the entire memory.

#### Program inhibit mode

Programming of multiple HT27LC512 in parallel with different data is also easily accomplished by using the Program Inhibit Mode. Except for  $\overline{CE}$ , all like inputs of the parallel HT27LC512 may be common. A  $\overline{TL}$  low-level program pulse applied to an HT27LC512  $\overline{CE}$  input with  $\overline{OE}/VPP=12.2\pm0.2V$  will program that HT27LC512. A

high-level CE input inhibits the other HT27LC512 from being programmed.

#### Program verify mode

Verification should be performed on the programmed bits to determine whether they were correctly programmed. The verification should be performed with  $\overline{\text{OE}}/\text{VPP}$  and  $\overline{\text{CE}}$  at  $V_{\text{IL}}$ . Data should be verified at  $t_{\text{DV}}$  after the falling edge of  $\overline{\text{CE}}$ .

#### Auto product identification

The Auto Product Identification mode allows the reading out of a binary code from an EPROM that will identify its manufacturer and type. This mode is intended for use by the programming equipment for the purpose of automatically matching the device to be programmed with its corresponding programming algorithm. This mode is functional in the 25°C±5°C ambient temperature range that is required when programming the HT27LC512.

To activate this mode, the programming equipment must force  $12.0\pm0.5V$  on the address line A9 of the HT27LC512. Two identifier bytes may then be sequenced from the device outputs by toggling address line A0 from V $_{\rm IL}$  to V $_{\rm IH}$ , when A1=V $_{\rm IH}$ . All other address lines must be held at V $_{\rm IH}$  during Auto Product Identification mode.

Byte 0 (A0=V<sub>IL</sub>) represents the manufacturer code, and byte 1 (A0=V<sub>IH</sub>), the device code. For HT27LC512, these two identifier bytes are shown in the Mode Select Table. All identifiers for the manufacturer and device codes will possess odd parity, with the MSB (DQ7) defined as the parity bit. When A1=V<sub>IL</sub>, the HT27LC512 will read out the binary code of 7F, continuation code, to signify the unavailability of manufacturer ID codes.



#### Read mode

The HT27LC512 has two control functions, both of which must be logically satisfied in order to obtain data at outputs. Chip Enable  $(\overline{\text{CE}})$  is the power control and should be used for device selection. Output Enable  $(\overline{\text{OE}})$  is the output control and should be used to gate data to the output pins, independent of device selection. Assuming that addresses are stable, address access time  $(t_{ACC})$  is equal to the delay from  $\overline{\text{CE}}$  to output  $(t_{CE})$ . Data is available at the outputs  $(t_{OE})$  after the falling edge of  $\overline{\text{OE}}$ , assuming the  $\overline{\text{CE}}$  has been LOW and addresses have been stable for at least  $t_{ACC}$ -to-E.

### Standby mode

The HT27LC512 has CMOS standby mode which reduces the maximum VCC current to  $10\mu A.$  It is placed in CMOS standby when  $\overline{CE}$  is at  $V_{CC^\pm}0.3V.$  The HT27LC512 also has a TTL-standby mode which reduces the maximum VCC current to 0.6mA. It is placed in TTL-standby when  $\overline{CE}$  is at  $V_{IH}.$  When in standby mode, the outputs are in a high-impedance state, independent of the  $\overline{OE}$  input.

#### Two-line output control function

To accommodate multiple memory connections, a two-line control function is provided to allow for:

- · Low memory power consumption
- Assurance that output bus contention will not occur. It is recommended that  $\overline{\text{CE}}$  be decoded and used as the primary device-selection function, while  $\overline{\text{OE}}$  be made a common connection to all devices in the array and connected to the READ line from the system control bus. This assures that all deselected memory devices are in their low-power standby mode and that the output pins are only active when data is desired from a particular memory device.

#### System considerations

During the switch between active and standby conditions, transient current peaks are produced on the rising and falling edges of Chip Enable. The magnitude of these transient current peaks is dependent on the output capacitance loading of the device. At a minimum, a 0.1  $\mu F$  ceramic capacitor (high frequency, low inherent inductance) should be used on each device between VCC and VPP to minimize transient effects. In addition, to overcome the voltage drop caused by the inductive effects of the printed circuit board traces on EPROM arrays, a 4.7  $\mu F$  bulk electrolytic capacitor should be used between VCC and VPP for each eight devices. The location of the capacitor should be close to where the power supply is connected to the array.

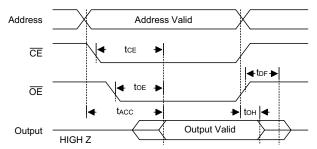


Figure 1. A.C. waveforms for read operation

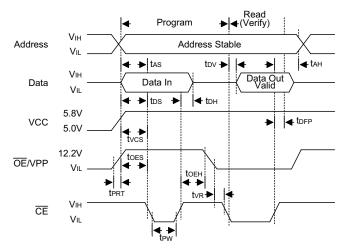
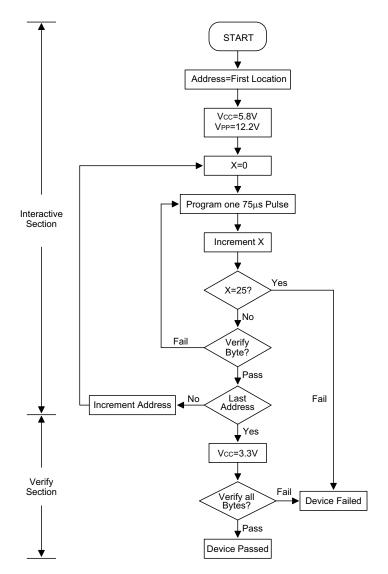


Figure 2. Programming waveforms





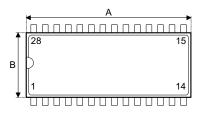
Note: Either 105  $\mu s$  or  $30 \mu s$  pulse.

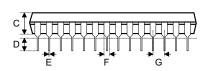
Figure 3. Fast programming flowchart

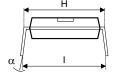


## **Package Information**

### 28-pin DIP (600mil) outline dimensions



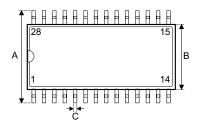


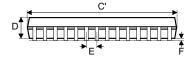


Complete	Dimensions in mil						
Symbol	Min	Nom	Max				
Α	1445	_	1465				
В	535	_	555				
С	145	_	155				
D	125	_	145				
Е	16	_	20				
F	50	_	70				
G	_	100	_				
Н	595	_	615				
I	635	_	670				
α	0°	_	15°				



### 28-pin SOP (300mil) outline dimensions



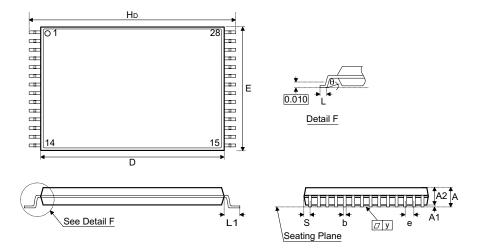




Combal	Dimensions in mil						
Symbol	Min	Nom	Max				
Α	394	_	419				
В	290	_	300				
С	14	_	20				
C'	697	_	713				
D	92	_	104				
E	_	50	_				
F	4	_	_				
G	32	_	38				
Н	4	_	12				
α	0°	_	10°				



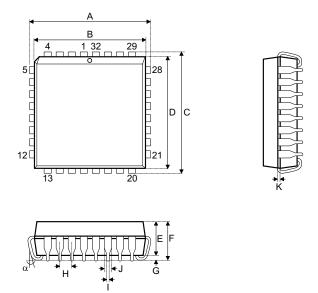
### 28-pin TSOP (8×13.4) outline dimensions



Comple at		Dimensions in mm						
Symbol	Min	Nom	Max					
А	_	_	1.25					
A1	0.08	_	0.18					
A2	0.95	_	1.05					
b	_	0.20	_					
D	11.70	_	11.90					
H <sub>D</sub>	13.20	_	13.60					
E	7.90	_	8.10					
е	_	0.55	_					
L	_	0.50	_					
L1	_	0.8	_					
θ	0°	_	5°					



### 32-pin PLCC outline dimensions



Sumb al		Dimensions in mil						
Symbol	Min.	Nom.	Max.					
Α	485	_	495					
В	445	_	455					
С	585	_	595					
D	545	_	555					
E	105	_	115					
F	_	_	140					
G	15	_	_					
Н	_	50	_					
I	16	_	22					
J	24	_	32					
К	8	_	12					
α	0°	_	10°					



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